

Pages 35 and 36, the paragraph bridging these pages from page 35, line 24 to page 36, line 12, replace the bridging paragraph with:

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In Fig. 24, there is shown a structure in which four present structures are repeatedly arranged to have sixteen thin film regions. In Fig. 25, moreover, there is presented an [electron-microscope photograph] illustration of a prototype element which is prepared by arranging the present structures repeatedly and by arranging memory cells of 120 bits in a matrix. In the photograph, ten control electrodes run transversely. Six sets of three low-resistance regions run longitudinally (which correspond to the low-resistance regions 1 to 3 such that two of them correspond to the thin film regions 1 and 2 for one control electrode). There are arranged  $10 \times 6 \times 2 = 120$  thin film regions. In this large-scale memory, the writing, erasing and reading methods can be accomplished basically in an identical manner.

IN THE ABSTRACT

Please cancel the Abstract and substitute therefor the Abstract of the Disclosure on the attached separate page.